General Purpose Transistor

PNP Silicon

Features

• These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	-45	Vdc
Emitter-Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current – Continuous	Ι _C	-100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^{\circ}C$	PD	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina	PD	300	mW
Substrate, (Note 2) $@T_A = 25^{\circ}C$ Derate above 25°C		2.4	mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

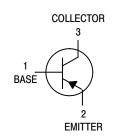
1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina



ON Semiconductor®

www.onsemi.com





SOT-23 (TO-236) CASE 318 STYLE 6

MARKING DIAGRAM



H2 = Device Code

= Pb–Free Package

(Note: Microdot may be in either location) *Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
BCW70LT1G	SOT–23 (Pb–Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

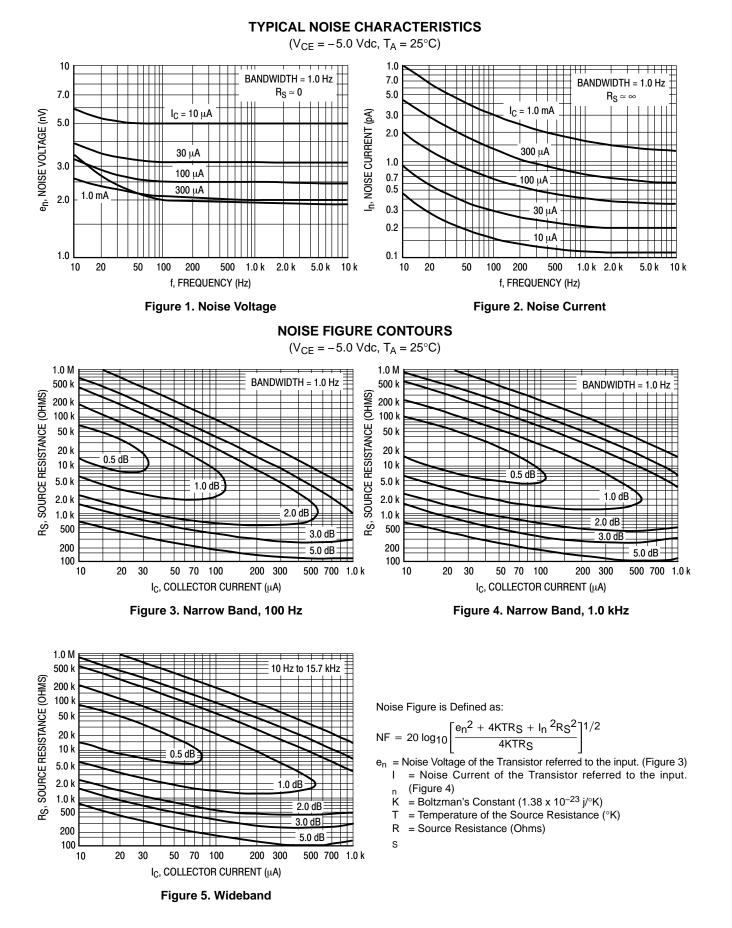
M = Date Code*

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

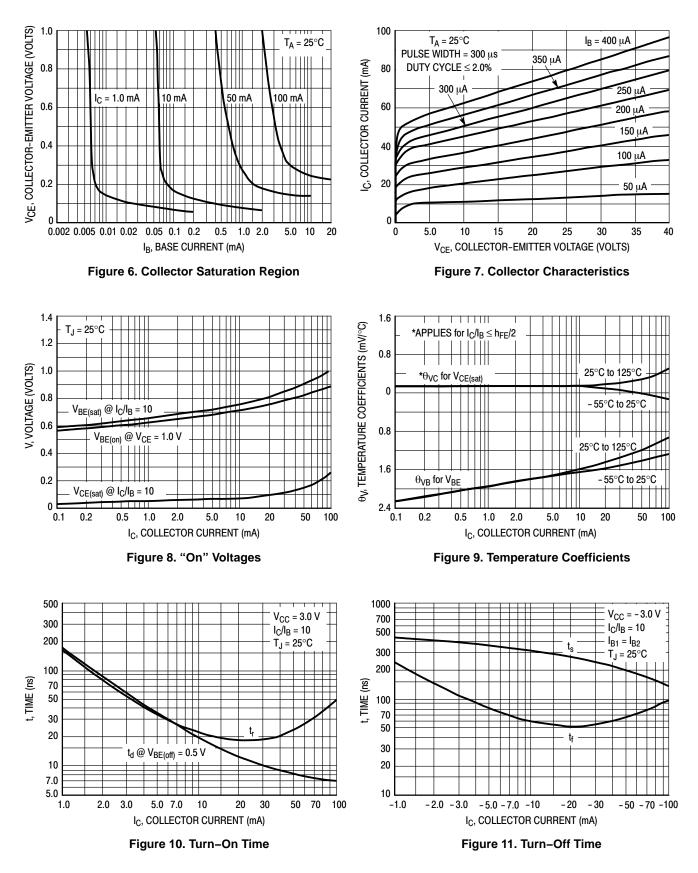
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				•
Collector–Emitter Breakdown Voltage $(I_{C} = -2.0 \text{ mAdc}, I_{B} = 0)$	V _{(BR)CEO}	-45	-	Vdc
Collector–Emitter Breakdown Voltage $(I_C = -100 \ \mu Adc, V_{EB} = 0)$	V _{(BR)CES}	-50	_	Vdc
Emitter–Base Breakdown Voltage ($I_E = -10 \ \mu Adc, I_C = 0$)	V _{(BR)EBO}	-5.0	_	Vdc
Collector Cutoff Current $(V_{CB} = -20 \text{ Vdc}, I_E = 0)$ $(V_{CB} = -20 \text{ Vdc}, I_E = 0, T_A = 100^{\circ}\text{C})$	І _{СВО}		-100 -10	nAdc μAdc
ON CHARACTERISTICS	ł	•	•	•
DC Current Gain $(I_C = -2.0 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc})$	h _{FE}	215	500	_
Collector–Emitter Saturation Voltage $(I_C = -10 \text{ mAdc}, I_B = -0.5 \text{ mAdc})$	V _{CE(sat)}	_	-0.3	Vdc
Base–Emitter On Voltage (I _C = -2.0 mAdc, V _{CE} = -5.0 Vdc)	V _{BE(on)}	-0.6	-0.75	Vdc
SMALL-SIGNAL CHARACTERISTICS		•	•	•

Output Capacitance ($I_E = 0$, $V_{CB} = -10$ Vdc, f = 1.0 MHz)	C _{obo}	-	7.0	pF
Noise Figure (I _C = -0.2 mAdc, V _{CE} = -5.0 Vdc, R _S = 2.0 k Ω , f = 1.0 kHz, BW = 200 Hz)	N _F	-	10	dB

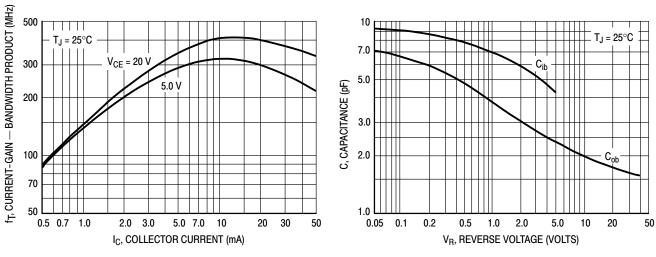
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



TYPICAL STATIC CHARACTERISTICS



TYPICAL DYNAMIC CHARACTERISTICS



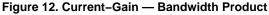
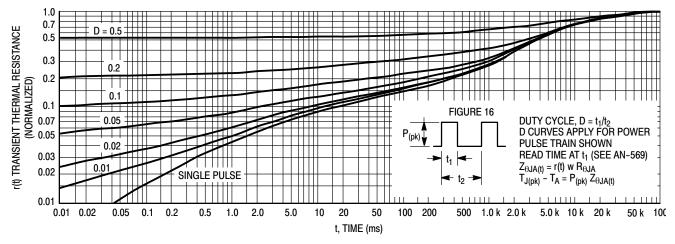


Figure 13. Capacitance





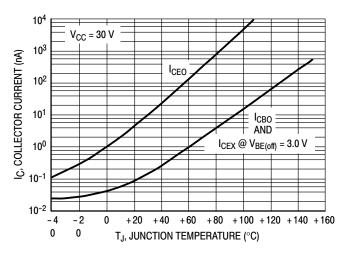


Figure 15. Typical Collector Leakage Current

DESIGN NOTE: USE OF THERMAL RESPONSE DATA

A train of periodical power pulses can be represented by the model as shown in Figure 16. Using the model and the device thermal response the normalized effective transient thermal resistance of Figure 14 was calculated for various duty cycles.

To find $Z_{\theta JA(t)},$ multiply the value obtained from Figure 14 by the steady state value $R_{\theta JA}.$

Example:

Dissipating 2.0 watts peak under the following conditions:

 $t_1 = 1.0 \text{ ms}, t_2 = 5.0 \text{ ms} (D = 0.2)$

Using Figure 14 at a pulse width of 1.0 ms and D = 0.2, the reading of r(t) is 0.22.

The peak rise in junction temperature is therefore

 $\Delta T = r(t) \times P_{(pk)} \times R_{\theta JA} = 0.22 \times 2.0 \times 200 = 88^{\circ}C.$

For more information, see AN–569.





© Semiconductor Components Industries, LLC, 2019

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and calcular performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

TECHNICAL SUPPORT

onsemi Website: www.onsemi.com

Email Requests to: orderlit@onsemi.com

North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support: Phone: 00421 33 790 2910 For additional information, please contact your local Sales Representative

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Onsemi: BCW70LT1 BCW70LT1G